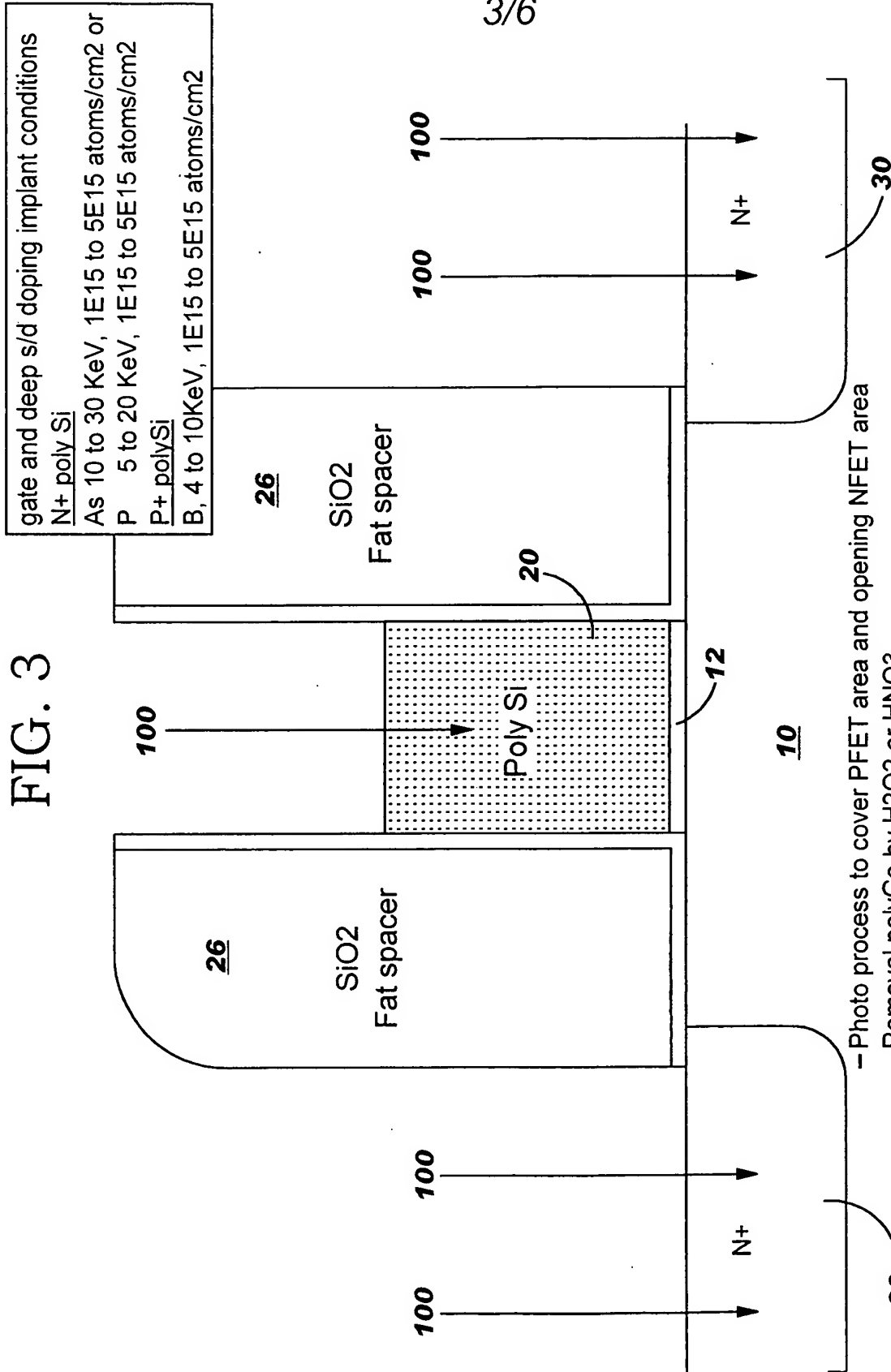


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- Photo process to cover PFET area and opening NFET area
- Removal polyGe by H2O2 or HNO3
- As or P deep implant to dope poly Si and deep n+ s/d
- Photo process to cover NFET area and opening PFET area
- Removal of poly Ge by H2O2 or HNO3
- B deep implant to dope polySi and deep p+ s/d

FIG. 4

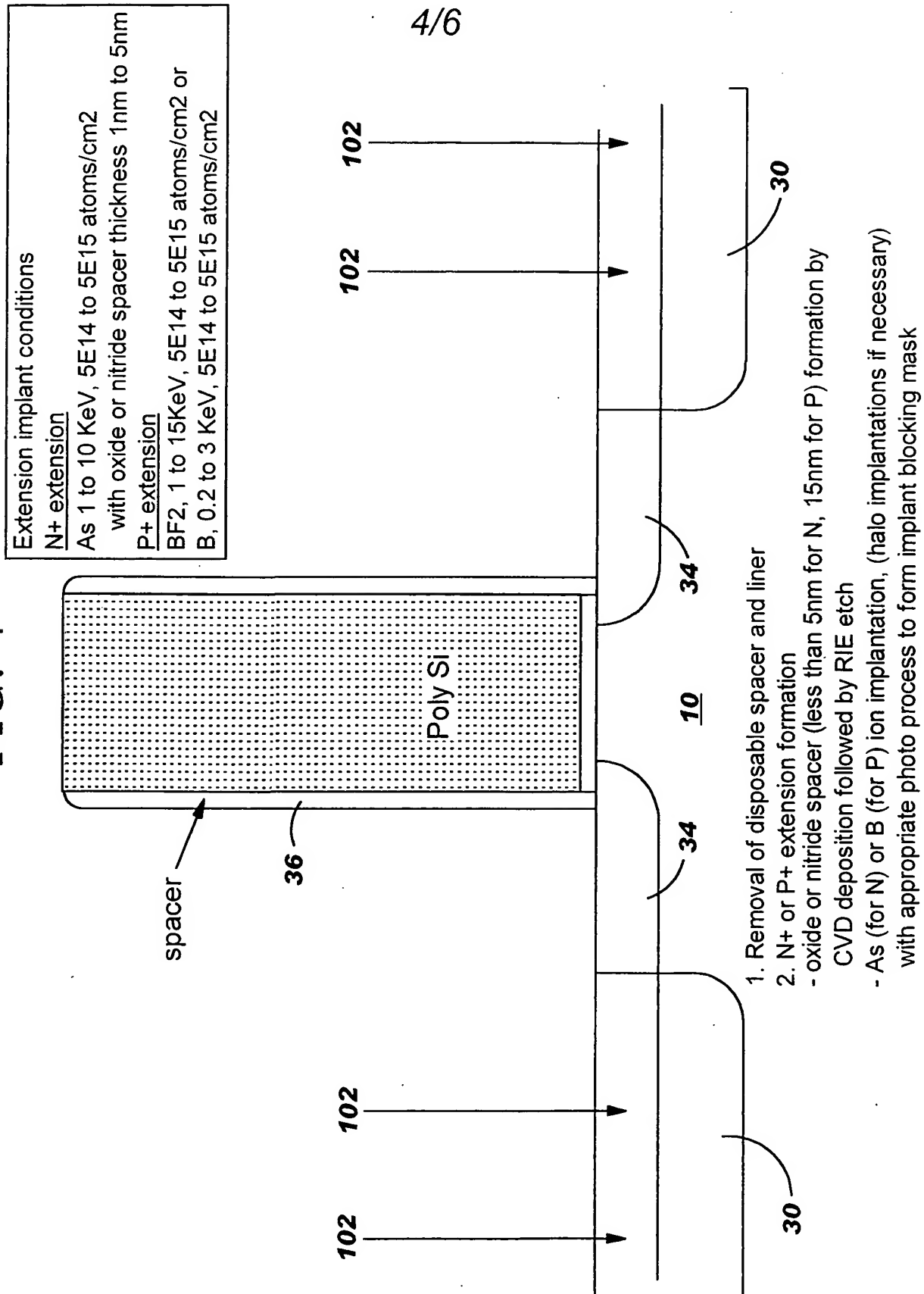
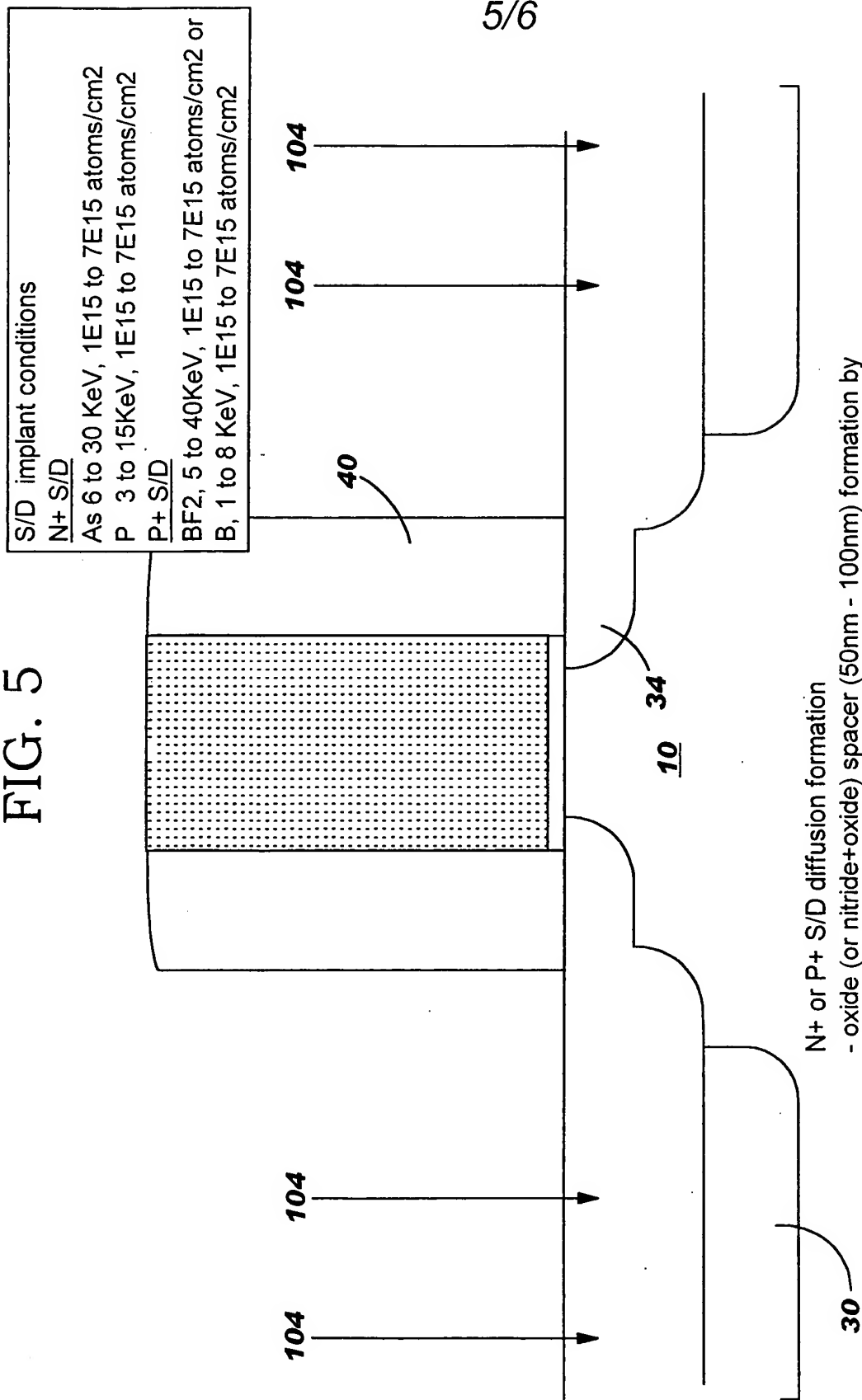


FIG. 5



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